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Originally published:

October 2018

Nanotechnology 29(2018)50, 504002

DOI: <https://doi.org/10.1088/1361-6528/aae281>

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To cite this article before publication: Jiajie Lin *et al* 2018 *Nanotechnology* in press <https://doi.org/10.1088/1361-6528/aae281>

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Efficient ion-slicing of InP thin film for Si-based hetero-integration

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Abstract

Integration of high quality single crystalline InP thin film on Si substrate has potential impact on Si-based photonics and high-speed electronics. In this work, the exfoliation of 634 nm crystalline InP layer from the bulk substrate was achieved by sequential implantation of He ions and H ions at room temperature. It is found that the sequence of He and H ions implantations has a decisive influence on the InP surface blistering and exfoliation, which only occurs in the InP pre-implanted with He ions. The exfoliation efficiency first increases and then decreases as a function of H ions fluence. With a kinetics analysis of the thermally activated blistering process, it suggests that the He and H ions sequential implantation can reduce the InP thin film splitting thermal budget dramatically. Finally, a high-quality 2-inch InP-on-Si (100) hetero-integration wafer was fabricated by He and H ions sequential implantation at room temperature in combination with direct wafer bonding.

Keywords: InP-on-Si, hetero-integration, ion-slicing, wafer bonding

1. Introduction

Monolithic integration of InP with Si substrate has attracted great interest thanks to the potential applications of combining InP based optoelectronic and high-speed electronic devices with the mature Si-based microelectronic circuits [1-3]. However, it is difficult to hetero-epitaxially grow high quality single crystalline InP thin film on Si substrate [4,5]. High density defects, e.g., the threading and misfitting dislocations, exist in the hetero-epitaxially grown InP thin film due to the lattice mismatch (8%) and thermal expansion coefficient mismatch (73.1%) between

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3 InP and Si [1,6], which limit the performance and reliability of optoelectronic and high-speed
4 electronic devices fabricated on the epitaxial layers.
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7 Alternatively, the ion-slicing technology appears to enable the generic development of high-
8 quality III-V semiconductors-on-Si hetero-integration by transferring the III-V layer from
9 crystal wafers to Si substrates. Ion slicing technology was first proposed by Bruel in 1995,
10 which has been successfully applied to the mass production of silicon-on-insulator (SOI) wafers
11 [7]. For the exploration of ion-slicing technology, it is the priority to realize the surface
12 blistering or exfoliation on the target crystal wafers by light elemental ion implantation (e.g.,
13 H, He ions implantation) combining with a post annealing process. In recent years, several
14 efforts have been made to achieve InP-on-Si hetero-integration materials by ion-slicing and
15 layer transferring process. The surface blistering or exfoliation of InP crystal wafers by either
16 H or He ion implantation has been reported [8-10]. Unlike Si, the exfoliation behavior of InP is
17 strongly depended on the ion implantation temperature. With single H ions implantation, the
18 InP surface blistering or exfoliation only occurs in two special implantation temperature
19 windows, i.e., a high implantation temperature window of 150°C-250°C and a low implantation
20 temperature window of -20°C-20°C [9,11]. However, it is difficult to control the implantation
21 temperature since it is sensitive to both of the physical contact between the target wafers and
22 sample holders and the ion implantation flux [10]. In the case of He ions implantation, a InP
23 layer was successfully transferred to Si substrate by He ions implantation at -15°C or 20°C with
24 a fluence of $5 \times 10^{16} \text{ cm}^{-2}$. However, nearly half thickness of the transferred InP layer was heavily
25 damaged due to the heavier He ion implantation with a high fluence and at low temperature.
26 Furthermore, with single H or He ions implantation, a post-annealing at relatively high
27 temperature of 200-400°C for long duration was required for the InP surface blistering or
28 exfoliation [9-12]. This will further increase the thermal stress between InP layer and Si
29 substrate due to the large thermal mismatch. Therefore, it is urgent to develop an efficient ion-
30 slicing process at room temperature for the high quality wafers-scale InP-on-Si hetero-
31 integration.
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36 In this study, the efficient exfoliation of InP thin film has been demonstrated by co-
37 implantation of He and H ions sequentially at room temperature. The sequential implantation
38 reduces the total ion fluence and thermal budget for the InP-on-Si hetero-integration by ion-
39 slicing and layer transferring process. Combining with the direct wafer bonding, a high quality
40 2-inch InP-on-Si hetero-integration wafer was successfully fabricated.
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46 **2. Experimental details**

47 He ions implantation with an energy of 115 KeV and H ions implantation with an energy of 75
48 KeV were carried out on 2-inch semi-insulating InP (100) wafers by sequence. Unless noted
49 otherwise, He ions implantation was carried out before H ions implantation. He ions
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3 implantation fluence was $2 \times 10^{16} \text{ cm}^{-2}$, while H ions implantation fluence varied from 3×10^{16}
4 cm^{-2} to $7 \times 10^{16} \text{ cm}^{-2}$. Both He and H ions implantations were carried out at room temperature.
5
6 In order to avoid the channeling effects, deliberate misalignment from the wafer normal of 7°
7 was performed during the implantation processes. After implantations, the InP wafers were
8 diced into small samples with the size of $10 \text{ mm} \times 10 \text{ mm}$ for the following characterizations.
9
10 Some of the samples were annealed to achieve the surface blistering or exfoliation. The surface
11 morphology of the samples was characterized by using an optical microscope (OM) of Leica
12 DM4000M. The crystalline quality was examined by X-ray diffraction (XRD) with a Philips
13 X'Pert X-ray diffractometer. The implantation-induced defects in the InP samples were
14 determined by Rutherford backscattering spectroscopy (RBS) using 1.7 MeV He ions at a
15 scatter angle of 170° and JEOL 2100F field-emission transmission electron microscopy (TEM).
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17 The cross-sectional scanning electron microscope (SEM) with Zeiss Supra55 was used to
18 characterize the InP-on-Si structure.
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26 3. Results and Discussions

27 After the He and H ions sequential implantation at room temperature, there is no significant
28 change on the surface of the implanted InP (not shown). The surface blistering and exfoliation
29 of the implanted InP occur after a post-annealing process at 150°C for 1 hour. It is found that
30 the implanted InP with varied H ions fluences show different exfoliation behaviors. The insets
31 in Fig. 1 (a) show the OM images of the surface morphology for the He and H ions sequentially
32 implanted InP with different H ions fluence. All the samples were post-annealed at 150°C for
33 1 hour. At low H ions fluence of $3 \times 10^{16} \text{ cm}^{-2}$ no blistering or exfoliation was observed on the
34 InP surface. Huge amounts of surface blistering appears as the H ions fluence was increased to
35 $4 \times 10^{16} \text{ cm}^{-2}$, and the large area surface exfoliation starts when the fluence is increased to 5×10^{16}
36 cm^{-2} . Surprisingly, no blistering occurs on the sample surface implanted with the highest H ions
37 fluence of $7 \times 10^{16} \text{ cm}^{-2}$. In order to quantitatively evaluate the InP exfoliation behavior, a
38 parameter of exfoliation efficiency A_{ex} was introduced to quantify the exfoliation [13]. The
39 exfoliation efficiency is defined as $A_{ex} \% = \frac{A_{ex}^{total}}{A_{sample}^{total}} \cdot 100\%$, where A_{ex}^{total} is the sum of the
40 individual exfoliation areas, and A_{sample}^{total} is the area of the entire OM image. Fig. 1 (a) shows
41 the exfoliation efficiency of implanted InP with different H ions implantation fluence. With
42 increasing H ions fluence, the exfoliation efficiency presents a Gaussian-like distribution and
43 reaches a maximum value of 90.6% at H ions fluence of $5 \times 10^{16} \text{ cm}^{-2}$.
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56 The exfoliation efficiency A_{ex} is related to efficient exfoliation cavities introduced by the
57 implanted ions [13]. With H ions fluence below $3 \times 10^{16} \text{ cm}^{-2}$, the internal pressure of the
58 efficient exfoliation cavities induced by H ions implantation is limited. Thus, there is no surface
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blistering or exfoliation observed on the InP surface even after the post-annealing process. By increasing the H ions fluence to $4 \times 10^{16} \text{ cm}^{-2}$, the internal pressure of the efficient exfoliation cavities is beyond the threshold for the surface blistering on the InP wafers. By further increasing the H ions fluence, a cleavage assisted coalescence between neighbor efficient exfoliation cavities occurs during the post-annealing process due to the large stress introduced by high fluence H ions implantation. And the internal pressure of the efficient exfoliation cavities is large enough to overcome the fracture stress of InP, which results in the large area surface exfoliation. In general, the nucleation of exfoliation efficiency cavities will be heightened with increasing H ions implantation fluence [14]. Hence, by increasing the H ions implantation fluence from $3 \times 10^{16} \text{ cm}^{-2}$ to $5 \times 10^{16} \text{ cm}^{-2}$, the exfoliation efficiency of InP increases. However, when the H ions implantation fluence is larger than $5 \times 10^{16} \text{ cm}^{-2}$, the exfoliation efficiency decreases with the increasing H ions implantation fluence. There is even no surface blistering or exfoliation observed on the InP crystal wafer with H ions fluence over $6 \times 10^{16} \text{ cm}^{-2}$. The similar exfoliation behaviors were also observed in Si by H and He ions sequential implantation [15].

In order to understand the underlying mechanism of the observed exfoliation behavior, the InP samples with He and H ions sequential implantation at room temperature (without the post-annealing process) were examined by XRD. Fig. 1 (b) shows the $(\omega/2\theta)$ XRD scans along the InP (004) reflection. In comparison to the XRD curve of the virgin InP crystal wafer, the implanted InP samples present additional scattered intensity with fringe pattern for the angles lower than the Bragg's angle, which indicates that there is out-of-plane tensile strain gradient with Gaussian-like shape induced by the ion implantation [16]. The periodicity of the fringe is related to the width of the strain layer and the most distant fringe from the Bragg's angle corresponds to the maximum stain in InP samples. Both the lattice parameters of the unstrained InP substrate and strained layer follow the Bragg's law: $\lambda = 2 \cdot d_{sub} \cdot \sin(\theta_{B,sub})$ for the unstrained InP substrate; and $\lambda = 2 \cdot d_{layer} \cdot \sin(\theta_{B,sub} + \Delta\theta)$ for the strained layer. λ is the wavelength of the incident X-ray, d_{sub} is the lattice parameter of the unstrained InP substrate, d_{layer} is the strained lattice parameter of the strain layer, $\theta_{B,sub}$ is the Bragg's angle of the unstrained InP substrate, and the $\theta_{B,sub} + \Delta\theta$ is the Bragg's angle of the strained layer. Then, the strain ε is expressed by equation (1) [16].

$$\varepsilon = \frac{d_{layer} - d_{sub}}{d_{sub}} = \frac{\sin(\theta_{B,sub})}{\sin(\theta_{B,sub} + \Delta\theta)} - 1 \quad (1)$$

Fig. 1 (c) shows the plot of maximum strain as a function of H ions fluence extracted from Fig. 1 (b). With the increase of the H ions fluence, the value of maximum strain first increases and then decreases as the H ions fluence is beyond $5 \times 10^{16} \text{ cm}^{-2}$, which is in the agreement with the results of the exfoliation efficiency shown by the red curve in Fig. 1 (a). It is well believed that the implantation induced lattice strain in the crystalline structure increases with increasing

implantation fluence. However, the implanted crystal will be partially decrystallized with excessive implantation [17], which releases the implantation lattice strain instead. Therefore, the maximum strain decreases when the H ions implantation fluence is over $5 \times 10^{16} \text{ cm}^{-2}$. It is reported that the implantation introduced out-of-plane strain promotes the nucleation and growth of platelet defects, meanwhile, out-of-plane strain is also a driving force for migration of platelet defects [18]. During the post-annealing process, the platelet defects migrate to coalesce with each other, which results in the surface exfoliation. As the H ions fluence beyond $5 \times 10^{16} \text{ cm}^{-2}$, the implantation induced strain is released and the growth and migration of the platelet defects are unmotivated, resulting in less exfoliations or even no exfoliation on the surface of samples after annealing.

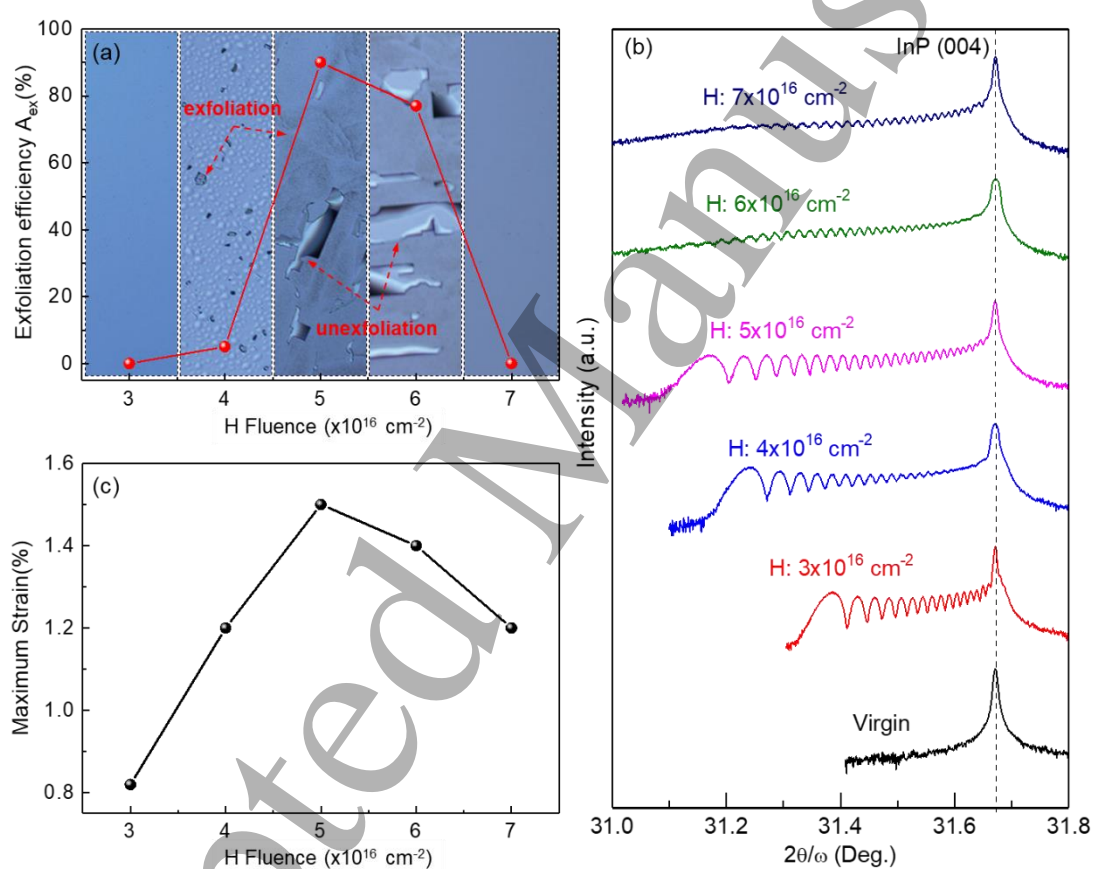


Fig. 1 (a) Exfoliation efficiency as a function of H ions implantation fluence for the He and H ions sequentially implanted InP after annealing at 150 °C for 1 hour. The insets show the corresponding OM images of the surface morphology. (b) ω -2 θ scan XRD curves along the InP (004) reflection for He and H ions co-implanted InP with different H ions implantation fluence. (c) The maximum strain as a function of H ions implantation fluence extracted from the XRD measurements.

In addition to the implantation fluence, the implantation sequence of He and H ions has a

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3 great influence on the InP surface blistering or exfoliation as well. Fig. 2 (a) and (b) show the
4 OM images of the InP surface with different implantation sequence of He and H ions after a
5 post-annealing at 150 °C for 1 hour. The He and H ions implantation fluences are $2 \times 10^{16} \text{ cm}^{-2}$
6 and $5 \times 10^{16} \text{ cm}^{-2}$, respectively. Large area exfoliation appears on the surface of sample pre-
7 implanted with He ions as shown in Fig. 2 (a), but no exfoliation or blistering is observed on
8 the surface of sample pre-implanted with H ions as shown in Fig. 2 (b). As shown in Fig. 2 (c),
9 Rutherford backscattering spectroscopy (RBS) in channeling mode was performed to study the
10 implantation-induced defects in the InP samples with different implantation sequence of He and
11 H ions. For comparison, the random and channeling RBS spectra of the virgin InP sample are
12 also presented. There is an evident damage peak at the channel number of 618 for all implanted
13 InP samples. The damage peak for the samples pre-implanted with H ions is higher than that of
14 the sample pre-implanted with He ions, which indicates that H ions pre-implantation followed
15 by He ions implantation introduce heavier lattice damages in comparison with the case of He
16 ions pre-implantation followed by H ions implantation. After post-annealing at 150°C for 6 min,
17 the damage peak for the sample pre-implanted with He ions increases significantly, which
18 suggests a defect evolution during the post-annealing process. However, there is no obvious
19 change for the sample pre-implanted with H ions before and after the post-annealing process.
20 As shown in Fig. 2 (d) and (e), cross-sectional TEM was utilized to analyze the microstructure
21 around the mean projected range of the ion implantation for the implanted InP samples after
22 post-annealing at 150 °C for 6 min. Some platelet defects, which are parallel to the surface of
23 the samples, appear around the mean projected range of the ion implantation for InP sample
24 pre-implanted with He ions as shown in Fig. 2 (d). He ions implantation with a relatively low
25 fluence would create a certain amount of open volume defects as the H ions trapping layer in
26 the InP crystal [19]. The subsequent implanted H ions can be attracted into the open volume
27 defects and increase the internal pressure of the open volume defects. With post-annealing, the
28 implanted H ions aggregate into the open volume defects due to the Oswald ripening effect,
29 and facilitate the open volume defects growing up to be platelet defects. The nucleation and
30 growth of platelet defects increase the dechanneling level, which results in the increase of the
31 damage peak in RBS spectra for the sample pre-implanted with He ions [19-21]. Moreover, the
32 platelet defects serve as the precursors of the micro-cracks which are essential for the surface
33 exfoliation [22]. However, the platelets defect was not observed in the InP samples pre-
34 implanted with H ions as shown in Fig. 2 (e). H ions implantation introduced mainly the tiny
35 point defects, like vacancy or vacancy cluster, rather than the large open volume defects, e.g.,
36 bubble or cavity, in the InP crystal. The small point defects prevent the formation of the large
37 open volume defects induced by the subsequent He ions implantation and obstruct the growth
38 of continues platelet defects parallel to the InP crystal surface. Therefore, large area surface
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exfoliation occurs in the sample pre-implanted with He ions as shown in Fig. 2 (a), but not in the sample pre-implanted with H ions as shown in Fig. 2 (b).

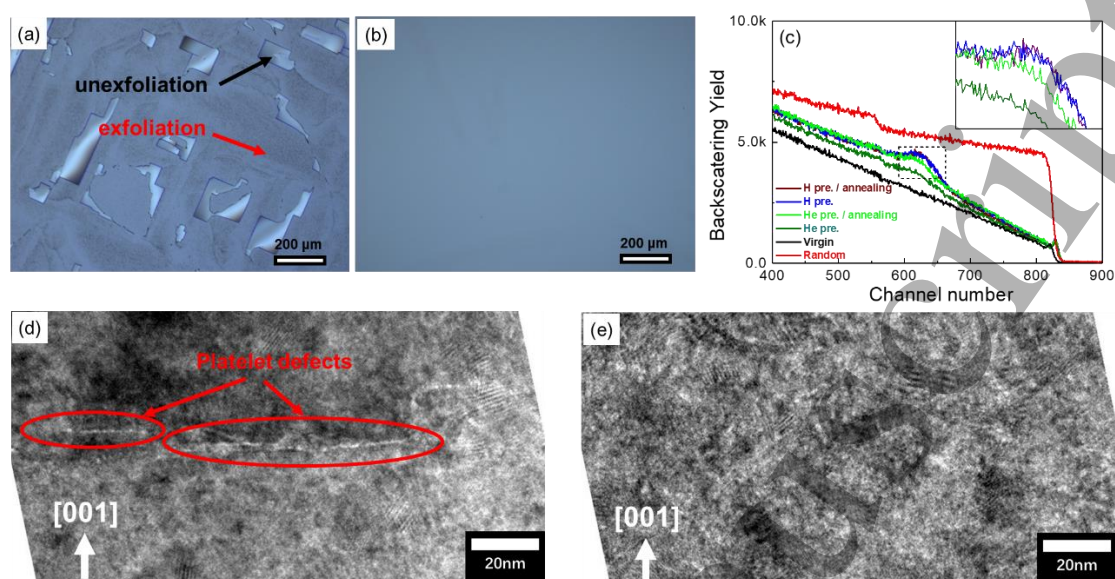


Fig. 2 OM images of the InP surface with different implantation sequence of He and H ions after a post-annealing at 150 °C for 1 hour. The He and H ions implantation fluences are $2 \times 10^{16} \text{ cm}^{-2}$ and $5 \times 10^{16} \text{ cm}^{-2}$, respectively. Large area exfoliation appears on the surface of sample pre-implanted with He ions (a), but no exfoliation or blistering was observed on the surface of sample pre-implanted with H ions (b). (c) RBS measurements for the InP samples with different implantation sequence of He and H ions. “Virgin” denotes the InP sample without ion implantation, “He pre.” denotes the InP sample pre-implanted with He, “He pre. / annealing” denotes the InP sample pre-implanted with He ions and post-annealed at 150 °C for 1 hour, “H pre.” denotes the InP sample pre-implanted with H, and “H pre. / annealing” denotes the InP sample pre-implanted with H ions and post-annealed at 150 °C for 6 min. Cross-sectional TEM images of the InP samples pre-implanted with He ions (d) and pre-implanted with H ions (e) after post-annealing 150 °C for 6 min.

A kinetics analysis of the thermally activated blistering process based on the Arrhenius relationship is essential to clarify the dependence of annealing parameters on the thermal evolution of blistering and exfoliations. The samples pre-implanted with He ions ($2 \times 10^{16} \text{ cm}^{-2}$) followed by H ions implantation ($5 \times 10^{16} \text{ cm}^{-2}$) were annealed with a Linkam THMS600 Temperature Controlled Stage and inspected in-suit with optical microscopy to determine the exfoliation time at different annealing temperature from 120 °C to 165 °C. Fig. 3 shows the Arrhenius plot of the exfoliation time as a function of reciprocal temperature in semi-log

coordinates, where longitudinal axis of the exfoliation time is in a log scale but the horizontal axis of reciprocal temperature is in a linear scale. Only one activation energy $E_a=0.427$ eV was extracted from the Arrhenius plot based on $1/t_b \propto \exp(-E_a/KT)$, where t_b is the onset time to form exfoliation and K is Boltzmann's constant and T is the absolute temperature [23]. There is no transition temperature where the activation energy changes abruptly, which was observed the InP with only He ions implantation [10]. In the case of GaAs blistering induced by H and He ions sequential implantation, there is no transition temperature as well and only one activation energy was extracted [14]. In comparison with InP blistering induced by only He ions implantation at low temperature (-15 °C) [10], the InP blistering with He and H ions sequential implantation in this work requires much lower activation energy (0.740 eV in Ref. [10], but 0.427 eV in this work) and much lower exfoliation temperature (over 200 °C in Ref. [10], but below 165 °C in this work). This suggests that the He and H ions sequential implantation can reduce the InP thin film splitting thermal budget dramatically. Additionally, the low exfoliation temperature can reduce the thermal strain in the InP-on-Si hetero-integration materials.

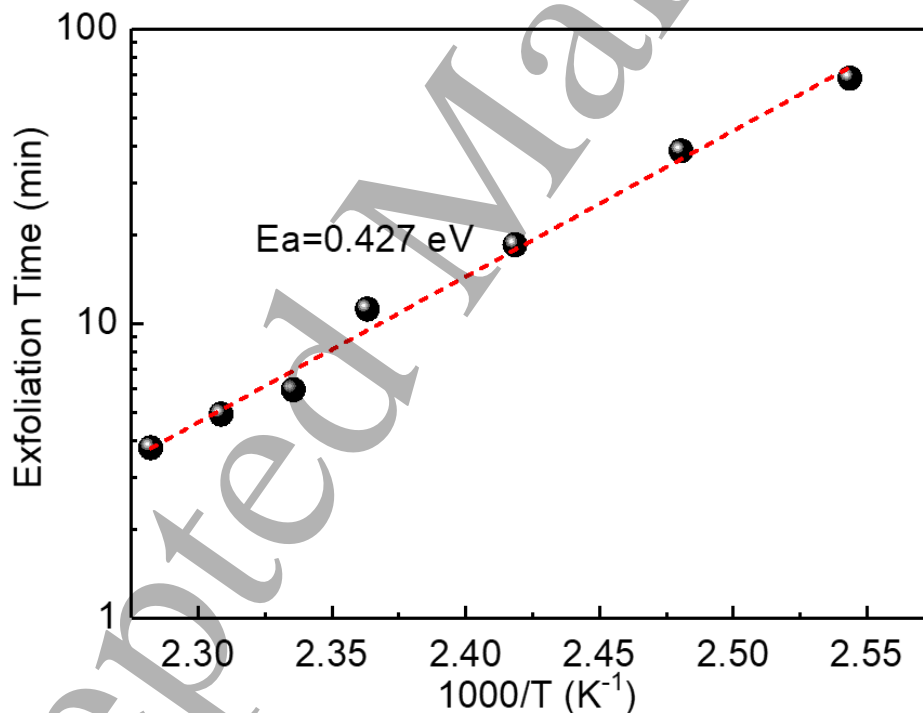


Fig. 3 Arrhenius plot of the exfoliation time as a function of reciprocal temperature for samples pre-implanted with He ions (2×10^{16} cm⁻²) followed by H ions implantation (5×10^{16} cm⁻²).

In order to achieve the wafer scale InP-on-Si hetero-integration, the He and H sequential implantation was carried out on a 2-inch InP wafer at room temperature. The ion energy/fluence of the He and H ions implantation are 115 KeV/ 2×10^{16} cm⁻² and 75 KeV/ 5×10^{16} cm⁻²,

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3 respectively. After the ion implantation and post-annealing, the surface blistering and exfoliation
4 occurred at the free surface to release the stress longitudinally. However, when a stiffener is bonded onto
5 the implanted crystal, the longitudinal relaxation of the stress is prevented, but the implantation induced
6 micro-cracks grow laterally which could result in the fracture and delamination of the whole layer [24-
7 26]. Therefore, the implanted InP wafer was bonded with a 4-inch SiO₂/Si(100) substrate
8 directly. Subsequently, the bonding pair of InP/SiO₂/Si wafers was annealed at 150°C for 1 hour
9 in N₂ atmosphere furnace. After annealing, a 2-inch InP layer was successfully transferred to
10 the Si substrate as marked with dashed circle in Fig. 4 (a), and the 2-inch InP donor wafer was
11 retained completely which can be recycled. A wafer-scale InP-on-Si hetero-integration material
12 was prepared. Fig. 4 (b) shows a typical cross-sectional scanning electron microscope (SEM)
13 image of the as-prepared InP-on-Si structure, which reveals a sharp and smooth interface
14 between the InP layer and SiO₂/Si substrate. The total thickness of the transferred InP thin film
15 is about 634 nm. The crystalline quality of the transferred InP thin film was evaluated by X-ray
16 rocking curves (XRCs) measurements. The normalized (004) XRCs for the bulk InP substrate
17 and as-transferred InP thin film are shown in Fig. 4 (c). The full width at half maximum (FWHM)
18 of the XRC is 61 arcsec for the transferred InP, which is slightly higher than the value of the
19 bulk InP substrate (16 arcsec). The broadened FWHM of transferred InP thin film is due to the
20 implantation-induced lattice disorder and a damaged surface layer. This is commonly observed
21 in the transferred thin film by ion-slicing process [27]. The profiles of the implantation induced
22 damage (displacement per atom, DPA) simulated by SRIM 2008 [28] are shown in Fig. 4 (d).
23 The red line indicates the DPA induced by the He and H ions sequential implantation performed
24 in this work, while the black line is the DPA induced by single He implantation with a fluence
25 of 5×10¹⁶ cm⁻² [28]. Both DPA profiles show Gaussian-like distribution, and the peak of the
26 profiles should be the exfoliation depth position. It is clear that the DPA induced by the He and
27 H ions sequential implantation is only half of that for the single He ion implantation, which
28 suggests that InP thin film with higher quality can be prepared by efficient ion-slicing process
29 with the He and H ions sequential implantation. Moreover, the FWHM of the as-transferred InP
30 thin film (61 arcsec) is even smaller than that of the heteroepitaxially grown InP thin film on
31 patterned Si substrates (75-540 arcsec) [29,30]. The implantation-induced lattice disorder is
32 possible to be recovered by an appropriate annealing process, and the damaged surface layer
33 can be removed by a chemical mechanical polishing (CMP) process. Therefore, the quality of
34 the transferred InP thin film can be further improved.
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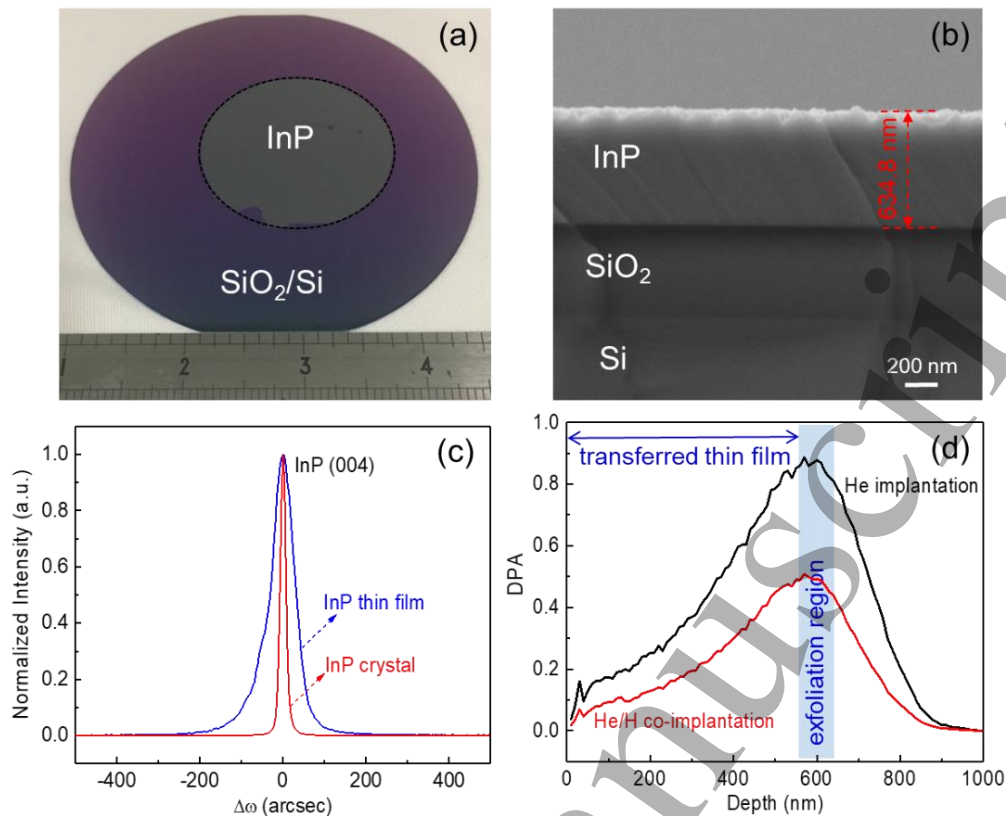


Fig. 4 (a) The image of 2-inch InP thin film transferred on SiO_2/Si substrate. The dashed circle roughs the area of the transferred InP thin film. (b) Typical cross-sectional SEM image of the as-prepared InP-on-Si hetero-integration material. (c) The normalized (004) XRCs for the virgin InP crystal and as-transferred InP thin film. (d) Implantation induced DPA profiles simulated by SRIM 2008.

4. Conclusions

In conclusion, we have demonstrated the efficient exfoliation of crystalline InP thin film by sequential implantation of He and H ions at room temperature. The thermal evolution of the implantation induced defects in InP crystals was investigated and the resulting surface blistering and exfoliation were characterized. With the increasing H ions implantation fluence, the exfoliation efficiency first increases and then decreases, which is consistent with implantation induced strain as revealed by XRD measurements. The surface exfoliation was only observed on the InP pre-implanted with He ions but not on the InP pre-implanted with H ions, which suggests that the sequence of He and H ions implantation plays a crucial role on the InP thin film splitting. The monolithic integration of high quality 2 inch InP thin film with 4 inch Si (100) substrate was achieved. The He and H ions sequential implantation can significantly reduce the InP thin film splitting thermal budget and introduce less implantation-induced defects in the transferred InP thin film. Efficient hetero-integration of InP on Si will serve as the platform for silicon-based photonic-electronic integration.

Acknowledgements

This work was supported by the National Natural Science Foundation of China (No.: 11705262, 11622545, U1732268 and 61674161), Frontier Science Key Program of CAS (No.: QYZDY-SSW-JSC032), One Hundred Talent Program of CAS, PuJiang Talent Program of Shanghai (No.: 17PJ1410500), International Collaboration Project of Shanghai (No.: 16520721100).

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